



STPS3060CW

POWER SCHOTTKY RECTIFIER

MAJOR PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x15 A
V_{RRM}	60 V
$V_F(\max)$	0.65 V

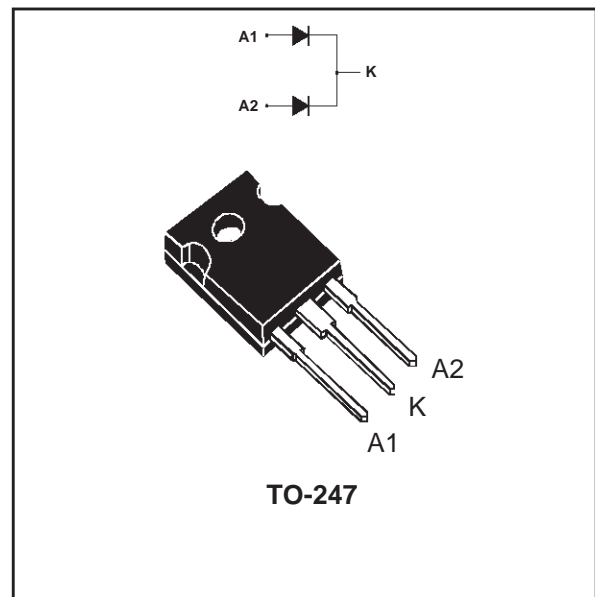
FEATURES AND BENEFITS

- HIGH REVERSE VOLTAGE
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE

DESCRIPTION

Dual center tap schottky rectifier suited for switchmode power supply and high frequency DC to DC converters.

Packaged in TO-247 this device is intended for use in high frequency inverters.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		60	V
$I_{F(RMS)}$	RMS forward current	Per diode	30	A
$I_{F(AV)}$	Average forward current	$T_c = 125^\circ\text{C}$ $\delta = 0.5$ Per diode Per device	15 30	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ Sinusoidal Per diode	200	A
I_{RRM}	Peak repetitive reverse current	$t_p = 2\ \mu\text{s}$ $F = 1\text{ kHz}$ Per diode	1	A
T_{stg}	Storage temperature range		- 65 to + 150	$^\circ\text{C}$
T_j	Maximum junction temperature		150	
dV/dt	Critical rate of rise reverse voltage		10000	V/ μs

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THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.6
		total	0.9
$R_{th(c)}$	Coupling	0.15	$^{\circ}\text{C}/\text{W}$

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_{j(\text{diode } 1)} = P(\text{diode } 1) \times R_{th(\text{Per diode})} + P(\text{diode } 2) \times R_{th(c)}$

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS PER DIODE

Symbol	Parameter	Tests Conditions	Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$			30	μA
		$T_j = 125^{\circ}\text{C}$		5	25	mA
V_F^{**}	Forward voltage drop	$T_j = 25^{\circ}\text{C}$			0.96	V
		$T_j = 125^{\circ}\text{C}$			0.8	
		$T_j = 125^{\circ}\text{C}$		0.58	0.65	

Pulse test : * $t_p = 5 \text{ ms}$, $\delta < 2 \%$

** $t_p = 380 \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.56 \times I_{F(AV)} + 0.0113 I_{F(RMS)}^2$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

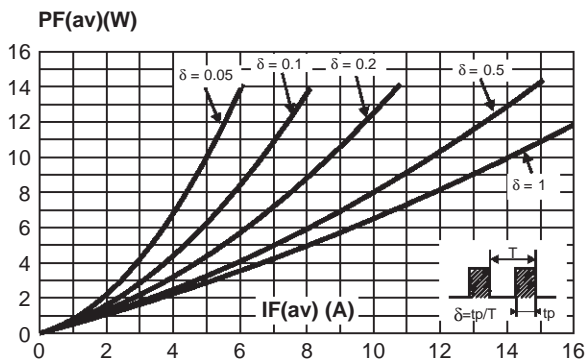


Fig. 2: Average current versus ambient temperature ($\delta = 0.5$) (per diode).

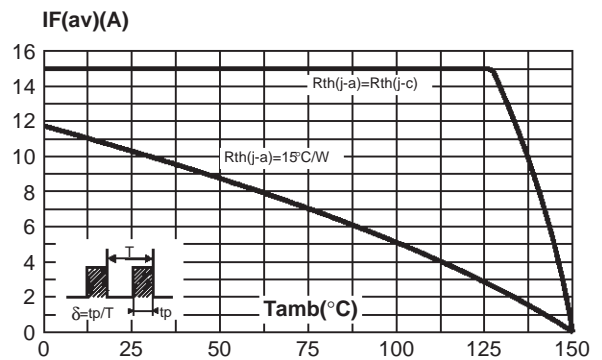


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values) (per diode).

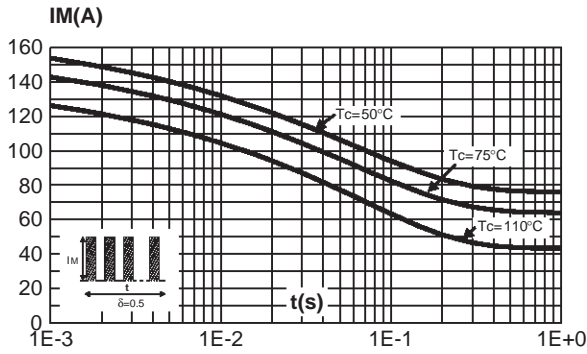


Fig. 4: Relative variation of thermal transient impedance junction to case versus pulse duration (per diode).

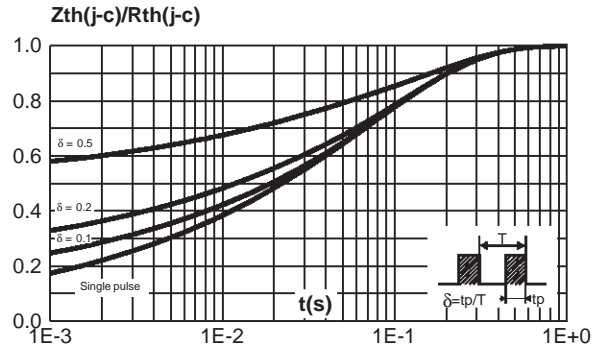


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values) (per diode).

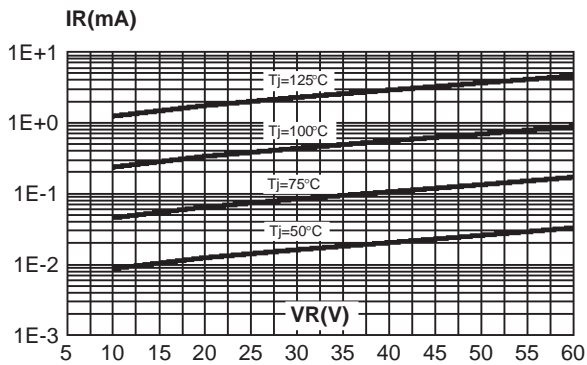


Fig. 6: Junction capacitance versus reverse voltage applied (typical values) (per diode).

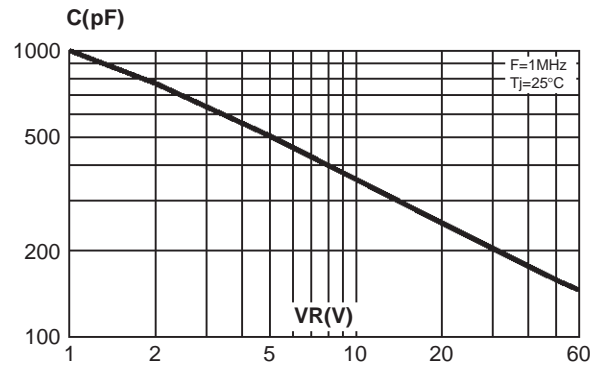
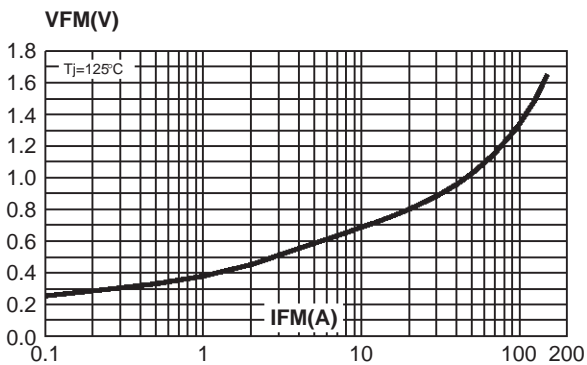
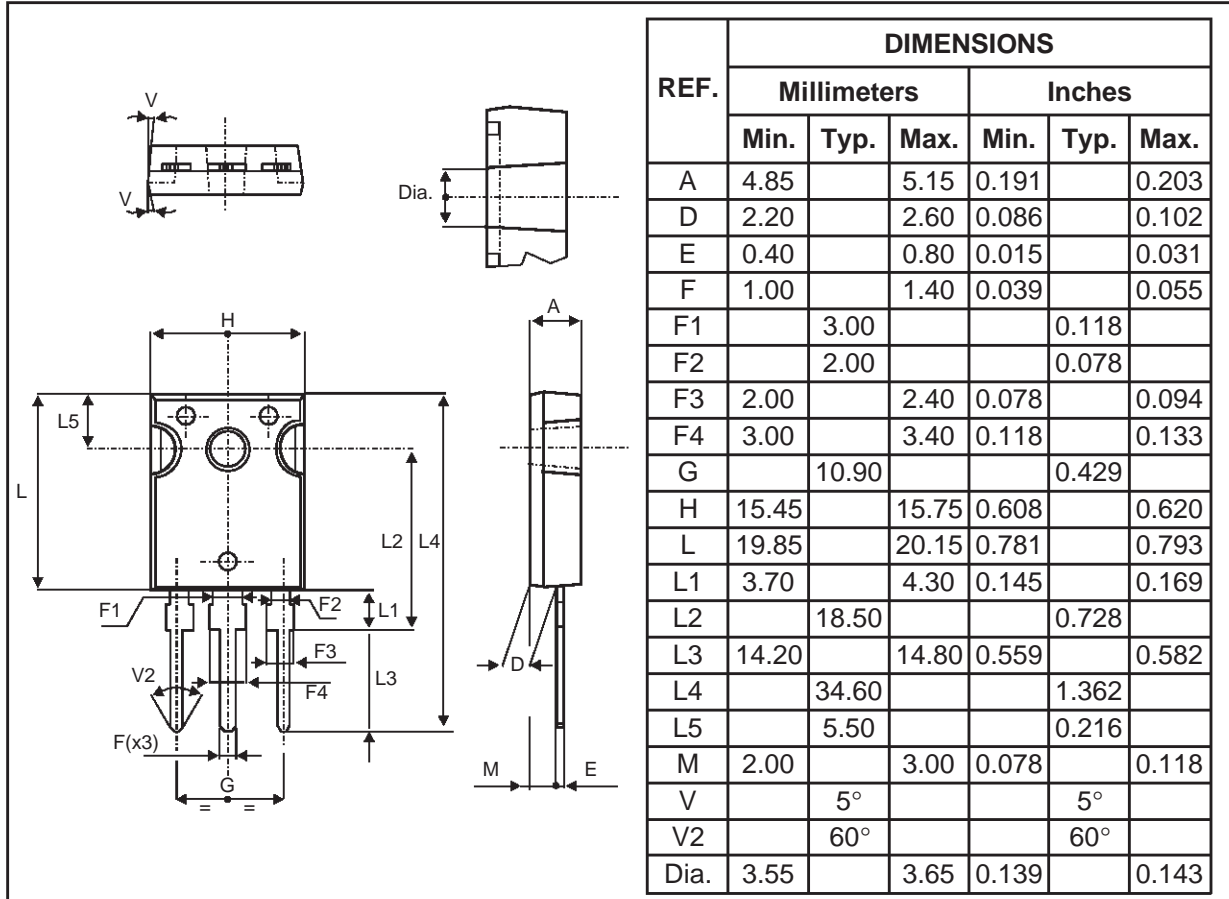


Fig. 7: Forward voltage drop versus forward current (maximum values) (per diode).



STPS3060CW

PACKAGE MECHANICAL DATA TO247



- **Marking:** STPS3060CW
- Cooling method : C
- Weight : 4.4 g
- Recommended torque value : 0.8m.N
- Maximum torque value : 1.0m.N

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